## SENSITRON SEMICONDUCTOR

TECHNICAL DATA DATA SHEET 4537, REV. A

# HERMETIC SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

### Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

#### **Maximum Ratings**

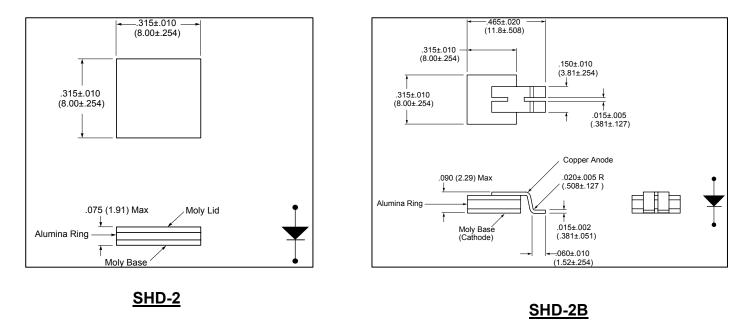
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V <sub>RWM</sub>	-	30	V
Max. Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle, rectangular wave form (Single)	30	A
Max. Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle, rectangular wave form (Common Cathode)	60	A
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine wave (per leg)	570	A
Non-Repetitive Avalanche Energy	$E_{AS}$	T <sub>J</sub> = 25 °C, I <sub>AS</sub> = 3.0 A, L = 4.4 mH (per leg)	20	mJ
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 µs f limited by $T_J$ max $V_A$ =1.5 $V_R$	3.0	A
Maximum Thermal Resistance	$R_{ ext{ heta}JC}$	DC operation	0.50	°C/W
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T <sub>stg</sub>	_	-65 to +150	°C

### **Electrical Characteristics**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V <sub>F1</sub>	@ 30A, Pulse, T <sub>J</sub> = 25 °C	0.49	V
(per leg)	V <sub>F2</sub>	@ 30A, Pulse, T <sub>J</sub> = 125 °C	0.39	V
Max. Reverse Current	I <sub>R1</sub>	$@V_R = 30V$ , Pulse,	4	mA
		T <sub>J</sub> = 25 °C		
(per leg)	I <sub>R2</sub>	$@V_R = 30V$ , Pulse,	200	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	CT	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C	2200	pF
(per leg)		f <sub>SIG</sub> = 1MHz,		
		V <sub>SIG</sub> = 50mV (p-p)		

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## **MECHANICAL DIMENSIONS: In Inches / mm**

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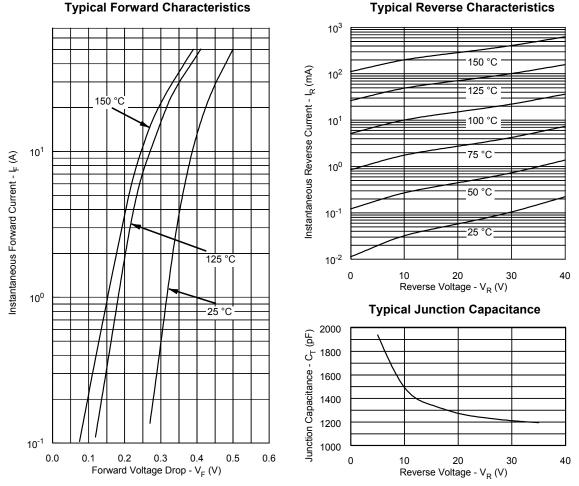
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**Note:** The V<sub>f</sub> curves shown are for the unpackaged die only.



#### **Typical Reverse Characteristics**